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Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	35 A				
V _{DRM} /V _{RRM}	1200 V				
V _{TM}	1.45 V				
I _{GT}	150 mA				
TJ	-40 °C to +125 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

FEATURES

- Low I_{GT}
- AEC-Q101 qualified meets JESD 201 class 1A RoHS
 whisker test
 COMPLIANT
- Flexible solution for reliable AC power FREE
 rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

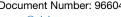
The VS-40TPS12.. high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	35	А			
I _{RMS}		55	~			
V _{RRM} /V _{DRM}		1200	V			
I _{TSM}		600	А			
V _T	40 A, T _J = 25 °C	1.45	V			
dv/dt		500	V/µs			
di/dt		100	A/µs			
TJ		- 40 to + 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-40TPS12ALHM3	1200	1300	10				

ABSOLUTE MAXIMUM RATINGS	;					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_C = 79 \ ^{\circ}C$, 180° conduction half sine wave	•	35		
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			55	А	
Maximum peak, one-cycle		10 ms sine pulse, rated V_{RRM} applied		500		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied		600		
Maximum I ² t for fusing	l ² t			1250	A ² s	
Maximum 1-t for fusing	1-1			1760	A-5	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	17 600	A²√s		
Low level value of threshold voltage	V _{T(TO)1}			1.02	V	
High level value of threshold voltage	V _{T(TO)2}			1.23	v	
Low level value of on-state slope resistance	r _{t1}	T _J = 125 °C		9.74	mΩ	
High level value of on-state slope resistance	r _{t2}			7.50	1112.2	
Maximum peak on-state voltage	V _{TM}	110 A, T _J = 25 °C		1.85	V	
Maximum rate of rise of turned-on current	di/dt	T _J = 25 °C		100	A/µs	
Maximum holding current	l _Η	Anode supply = 6 V, resistive load, initial T_J = 1 A, I_T = 25 °C		300		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		350		
Maximum variance and divect looks as associate		$T_J = 25 \text{ °C}$		0.5	mA	
Maximum reverse and direct leakage current	I _{RRM} /I _{DRM}	$V_{\rm R}$ = rated $V_{\rm RRM}/V_{\rm DR}$	Μ	10		
Maximum rate of rise of off-state voltage	dv/dt	$T_J = T_J$ maximum, linear to 80 % V _{DRM} , R_g -	k = 100 Ω	500	V/µs	

TRIGGERING							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}			10	W		
Maximum average gate power	P _{G(AV)}			2.5	vv		
Maximum peak gate current	I _{GM}			2.5	А		
Maximum peak negative gate voltage	-V _{GM}			10	V		
	V _{GT}	T _J = - 40 °C		2.0			
Maximum required DC gate voltage to trigger		T _J = 25 °C	Anode supply = 6 V resistive load	1.7	V		
		T _J = 125 °C		1.3			
		T _J = - 40 °C		150			
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	40	mA		
		T _J = 125 °C		20			
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °O M stated at a		0.15	V		
Maximum DC gate current not to trigger	I _{GD}	$I_J = I_2 \circ O, V_{DRM} = rated V$	$T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$		mA		





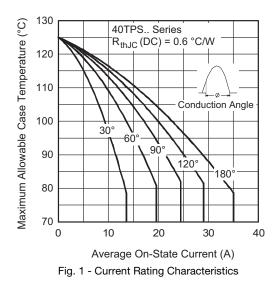
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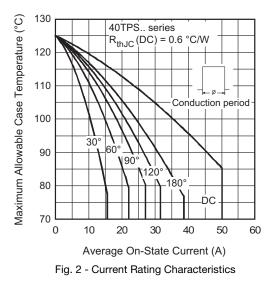
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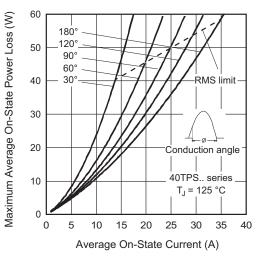
VS-40TPS12ALHM3

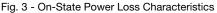
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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL TEST CONDITIONS		VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to + 125	°C			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.6	°C/W			
Maximum thermal resistance, junction to ambient	R _{thJA}	DC operation	40				
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth and greased	0.20				
Approximate weight			6	g			
Approximate weight			0.21	oz.			
Mounting torgueminimum			6 (5)	kgf · cm			
maximum			12 (10)	(lbf ⋅ in)			
Marking device		Case style TO-247AD 3L	40TPS12	ALH			









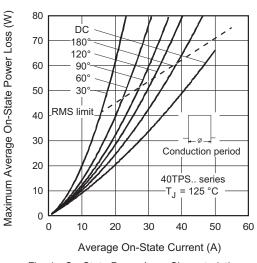


Fig. 4 - On-State Power Loss Characteristics

Revision: 13-May-2019

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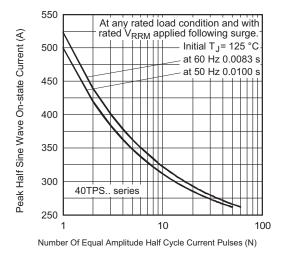
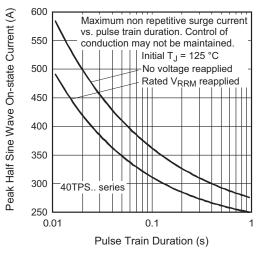
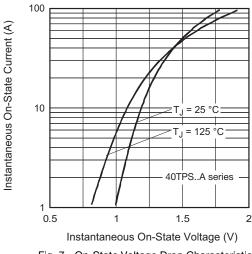
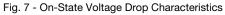


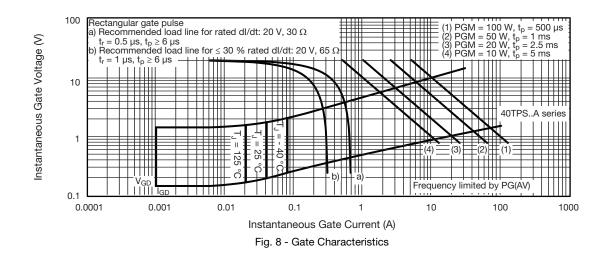
Fig. 5 - Maximum Non-Repetitive Surge Current











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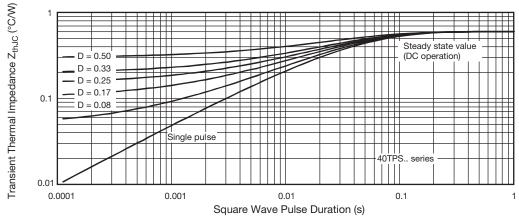


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

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SHAY

Device code	VS-	40	т	Р	S	12	Α	L	н	М3
	1	2	3	4	5	6	7	8	9	10
	1	- Visł	nay Sem	niconduc	ctors pro	duct				
	2	- Cur	rent rati	ng (40 =	40 A)					
	3	- Circ	uit conf	iguratior	n:					
		T =	thyristo	r						
	4	- Pac	kage:							
		P =	TO-247							
	5	- Тур	e of silio	con:						
	_				ery rectif	fier	г			
	6	- Volt	age rati	ngs —				12 = 12	200 V	
	7	- • A	= Low I	gt selec	tion 40 ı	mA max	timum			
	_				lgt seled	ction				
	8	- L=	long lea	ds						
	9	- H=	AEC-Q	101 qua	lified					
	10	- Env	vironmer	ntal digit	:					
		M3	= halog	en-free,	RoHS-c	compliar	nt, and f	erminat	ions lea	d (Pb)-fr

ORDERING INFORMATION (Example)							
PREFERRED P/N	PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TPS12ALHM3	25	500	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95626					
Part marking information www.vishay.com/doc?95007					

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TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INC	INCHES	
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	5 BSC	
ØК	0.2	254	0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	5.51 BSC		' BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

 Revision: 06-Mar-2020
 1
 Document Number: 95626

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Revision: 01-Jan-2025

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